

Silicon PNP Power Transistors

2N4898 2N4899 2N4900

DESCRIPTION

- With TO-66 package
- Low collector-emitter saturation voltage
- Excellent safe operating area
- 2N4900 complement to type 2N4912

APPLICATIONS

- Designed for driver circuits, switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

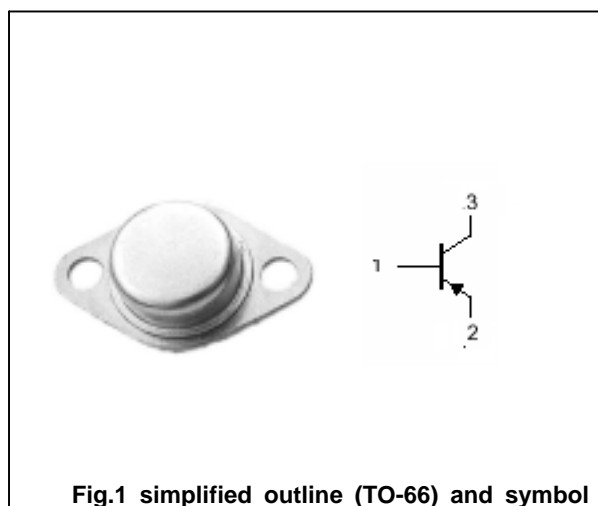


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	2N4898	40	V
		2N4899	60	
		2N4900	80	
V _{CEO}	Collector-emitter voltage	2N4898	40	V
		2N4899	60	
		2N4900	80	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		1.0	A
I _{CM}	Collector current-peak		4.0	A
I _B	Base current		1.0	A
P _D	Total Power Dissipation	T _C =25	25	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th-j-c}	Thermal resistance junction to case	7.0	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(sus)}	Collector-emitter sustaining voltage	2N4898	I _C =0.1A ; I _B =0			V
		2N4899				
		2N4900				
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A; I _B =0.1A			0.6	V
V _{BEsat}	Collector-emitter saturation voltage	I _C =1A ; I _B =0.1A			1.3	V
V _{BE}	Base-emitter on voltage	I _C =1A ; V _{CE} =1V			1.3	V
I _{CEO}	Collector cut-off current	2N4898			0.5	mA
		2N4899				
		2N4900				
I _{CEx}	Collector cut-off current	V _{CE} =Rated V _{CEO} ; V _{BE(off)} =1.5V T _C =150			0.1 1.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =Rated V _{CBO} ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =50mA ; V _{CE} =1V	40			
h _{FE-2}	DC current gain	I _C =500mA ; V _{CE} =1V	20		100	
h _{FE-3}	DC current gain	I _C =1.0A ; V _{CE} =1V	10			
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V; f=1MHz			100	pF
f _T	Transition frequency	I _C =250mA; V _{CE} =10V	3.0			MHz

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PACKAGE OUTLINE

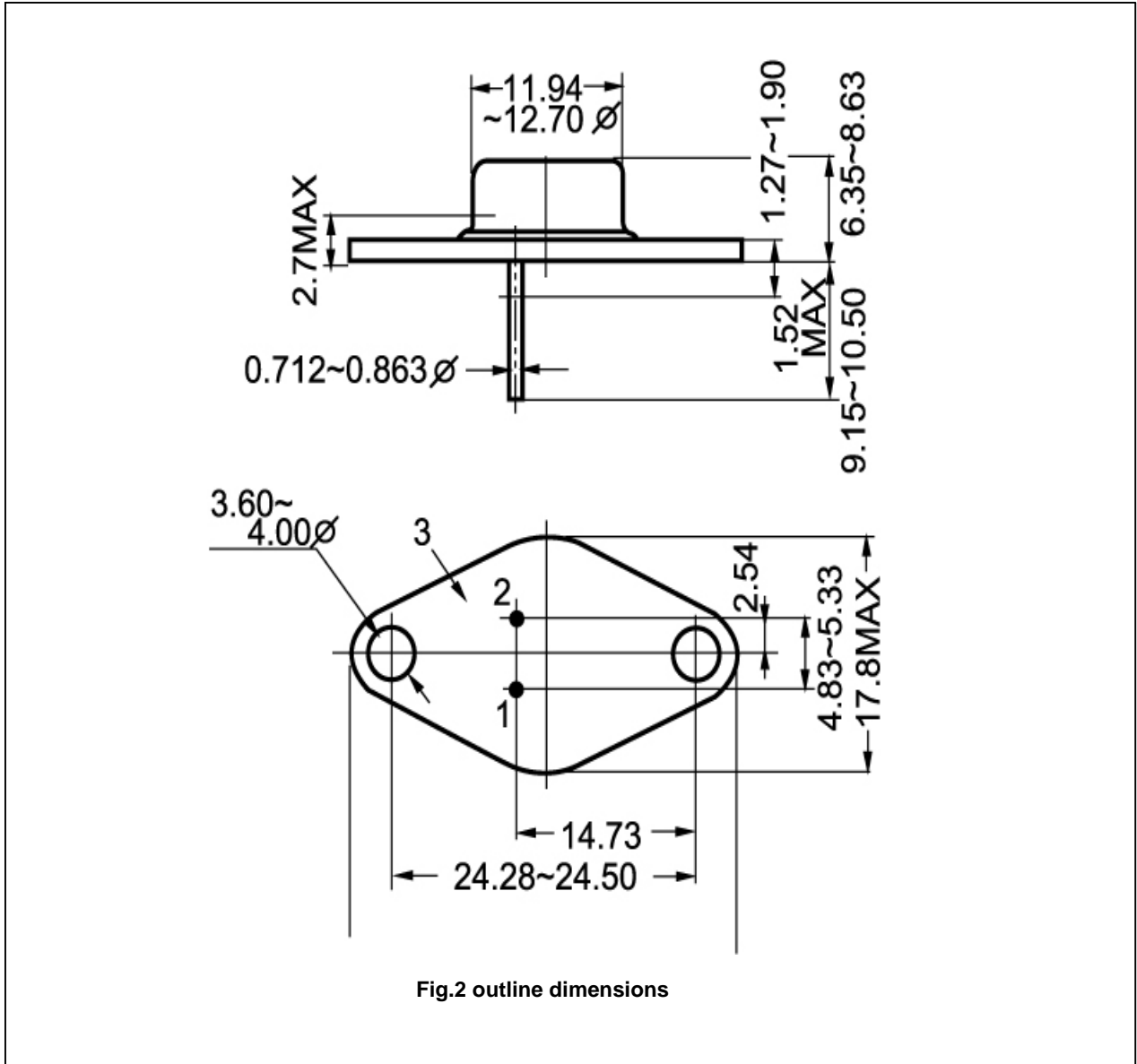


Fig.2 outline dimensions